



CST4614 N-Ch and P-Ch Fast Switching MOSFETs

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

CST4614 Product Summary

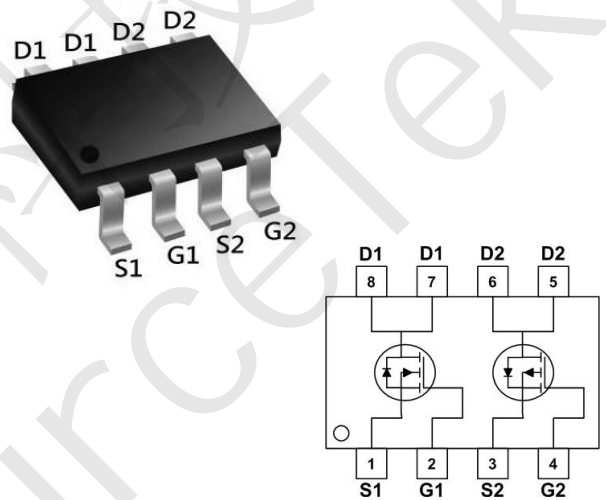


BVDSS	RDSON	ID
40V	17mΩ	8.5A
-40V	39mΩ	-7.5A

CST4614 Description

The CST4614 is the high performance complementary N-ch and P-ch MOSFETs with high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications. The CST4614 meet the RoHS and Green

CST4614 SOP8 Pin Configurations



CST4614 Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Symbol	Parameter	Max. N-Channel	Max. P-Channel	Units	
V _{DSS}	Drain-Source Voltage	40	-40	V	
V _{GSS}	Gate-Source Voltage	±20	±20	V	
I _D	Continuous Drain Current	T _A = 25°C	8.5	-7.5	A
		T _A = 100°C	5.2	-3.9	A
I _{DM}	Pulsed Drain Current ^{note1}	32	-24	A	
E _{AS}	Single Pulsed Avalanche Energy ^{note2}	13	17.6	mJ	
P _D	Power Dissipation	2	3.2	W	
R _{θJA}	Thermal Resistance, Junction to Ambient	62.5	39	°C/W	
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150		°C	



CST4614 N-Ch and P-Ch Fast Switching MOSFETs

CST4614 N-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=40V, V_{GS}=0V$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	$V_{GS}=10V, I_D=8A$	-	17	22	m Ω
		$V_{GS}=4.5V, I_D=5A$	-	25	35	m Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=20V, V_{GS}=0V,$ $f=1.0MHz$	-	633	-	pF
C_{oss}	Output Capacitance		-	67	-	pF
C_{rss}	Reverse Transfer Capacitance		-	58	-	pF
Q_g	Total Gate Charge	$V_{DS}=20V, I_D=8A,$ $V_{GS}=10V$	-	12	-	nC
Q_{gs}	Gate-Source Charge		-	3.2	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	3.1	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=20V, R_L=2.5\Omega$ $V_{GS}=10V, R_{REN}=3\Omega$	-	4	-	ns
t_r	Turn-on Rise Time		-	3	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	15	-	ns
t_f	Turn-off Fall Time		-	2	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	8.5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	32	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=8A$	-	-	1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : $T_J=25^\circ\text{C}, V_{DD}=20V, V_G=10V, L=0.5mH, R_g=25\Omega, I_{AS}=7.2A$

$T_J=25^\circ\text{C}, V_{DD}=-20V, V_G=-10V, L=0.5mH, R_g=25\Omega, I_{AS}=-8.4A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$



CST4614 N-Ch and P-Ch Fast Switching MOSFETs

CST4614 P-Channel Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -40V, V _{GS} =0V	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250μA	-1.0	-1.6	-2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note3</small>	V _{GS} = -10V, I _D = -6A	-	39	53	mΩ
		V _{GS} = -4.5V, I _D = -4A	-	58	81	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -20V, V _{GS} =0V, f=1.0MHz	-	860	-	pF
C _{oss}	Output Capacitance		-	87	-	pF
C _{rss}	Reverse Transfer Capacitance		-	70	-	pF
Q _g	Total Gate Charge	V _{DS} = -20V, I _D = -6A, V _{GS} = -10V	-	13	-	nC
Q _{gs}	Gate-Source Charge		-	3.8	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	3.1	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -20V, R _L =2.3Ω V _{GS} =-10V, R _{REN} =6Ω	-	7.5	-	ns
t _r	Turn-on Rise Time		-	5.5	-	ns
t _{d(off)}	Turn-off Delay Time		-	19	-	ns
t _f	Turn-off Fall Time		-	7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-7.5	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-24	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = -6A	-	-	-1.2	V



CST4614 Typical Performance Characteristics-N

Figure 1: Output Characteristics

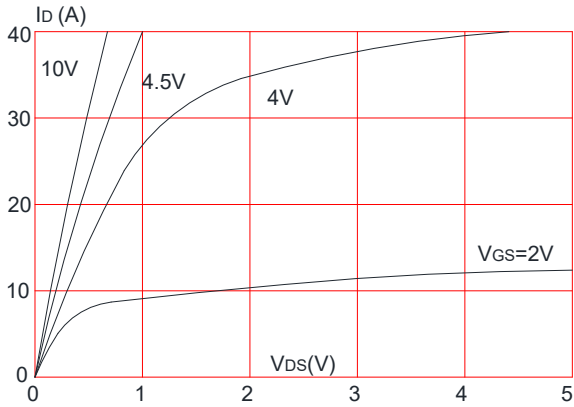


Figure 2: Typical Transfer Characteristics

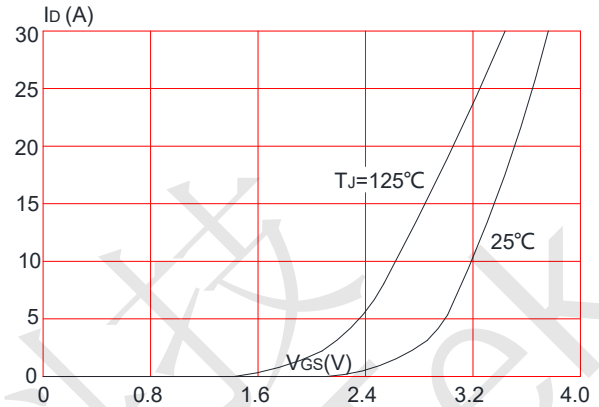


Figure 3: On-resistance vs. Drain Current

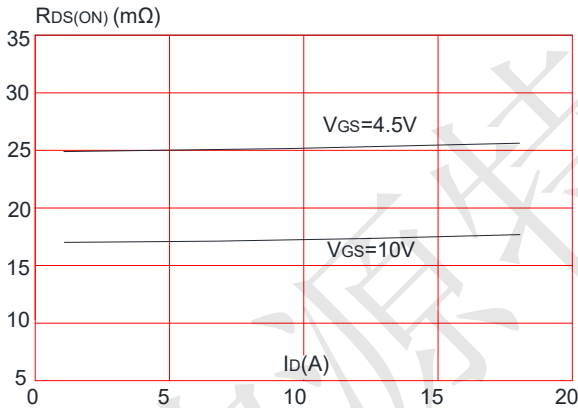


Figure 4: Body Diode Characteristics

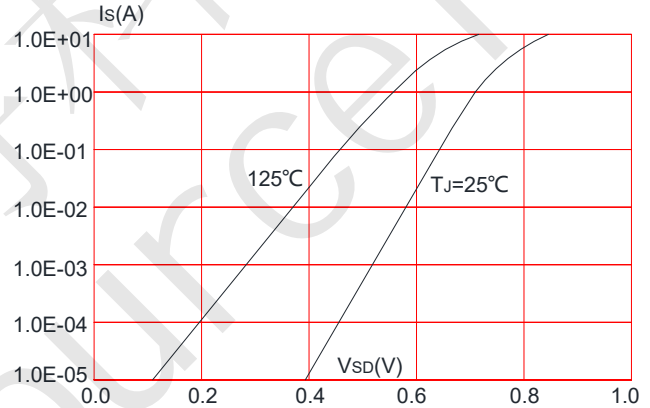


Figure 5: Gate Charge Characteristics

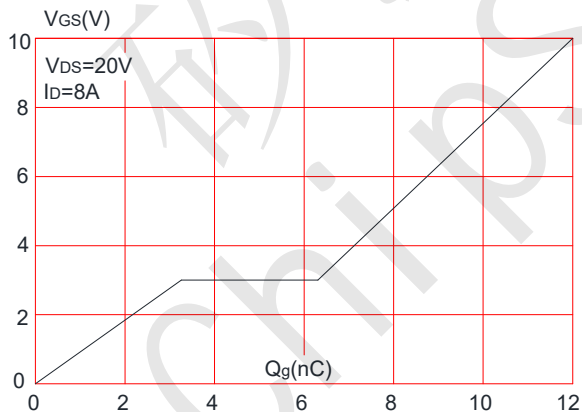
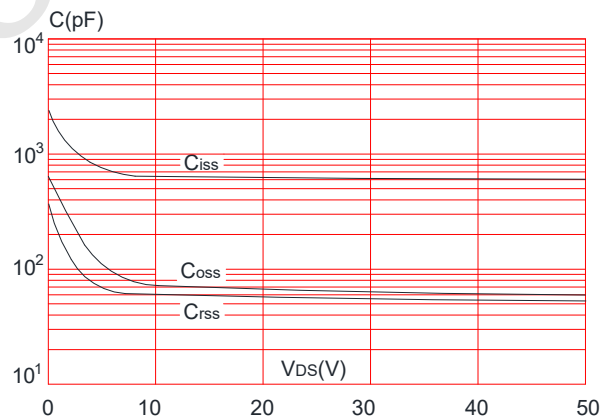


Figure 6: Capacitance Characteristics





CST4614 N-Ch and P-Ch Fast Switching MOSFETs

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

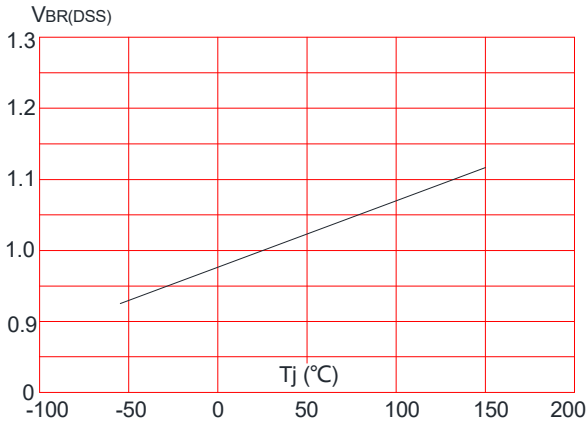


Figure 8: Normalized on Resistance vs. Junction Temperature

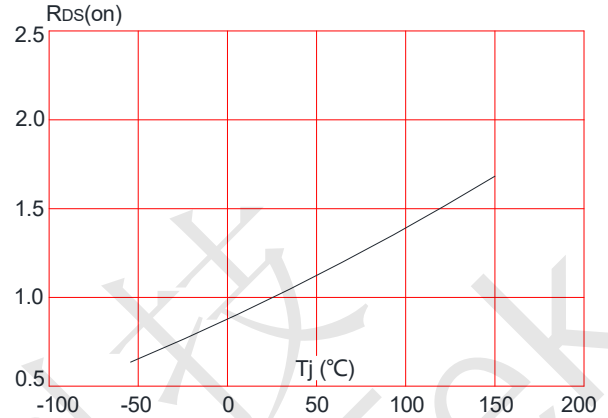


Figure 9: Maximum Safe Operating Area

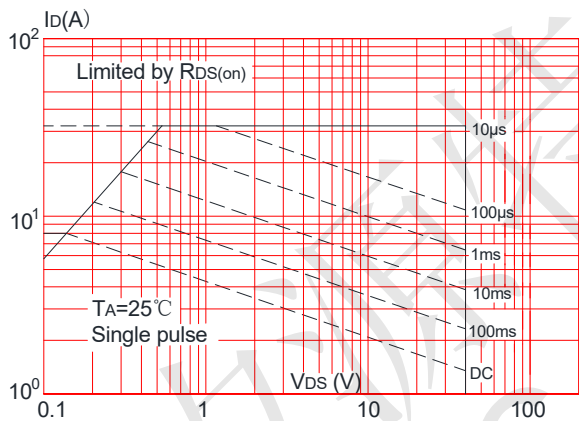


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

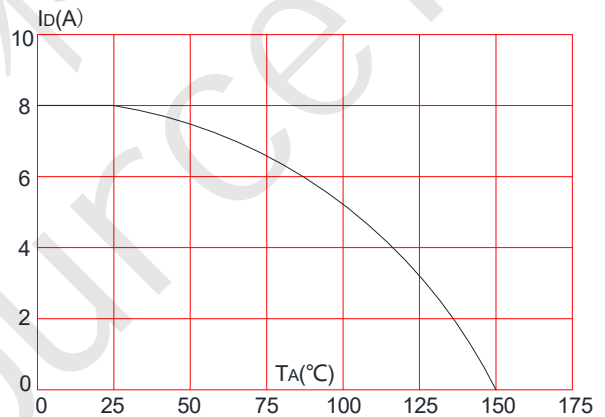
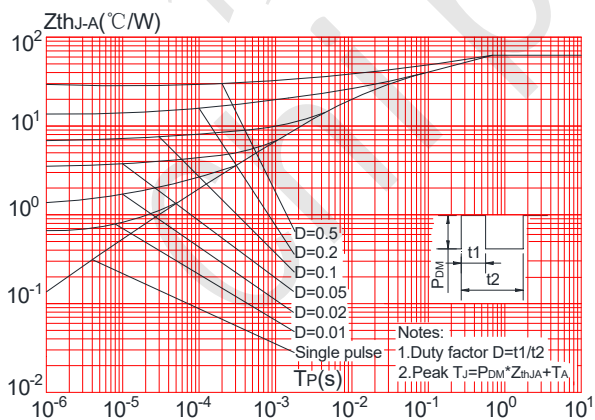


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





CST4614 Typical Performance Characteristics-P

Figure 1: Output Characteristics

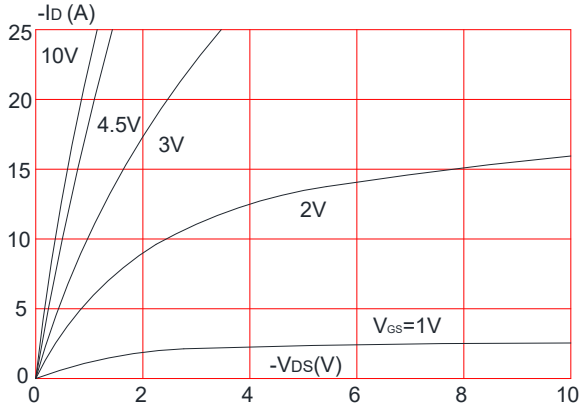


Figure 2: Typical Transfer Characteristics

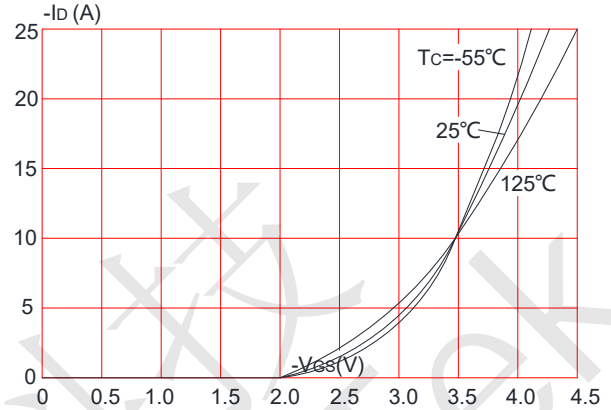


Figure 3: On-resistance vs. Drain Current

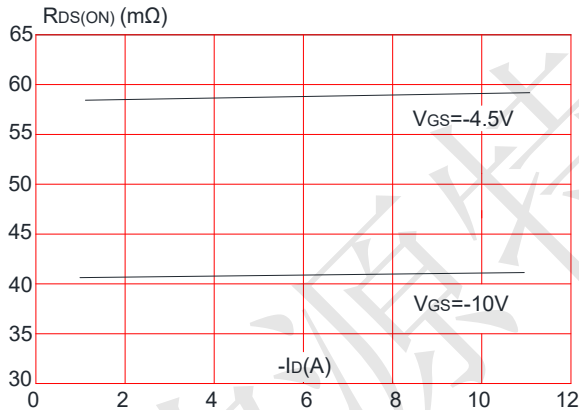


Figure 4: Body Diode Characteristics

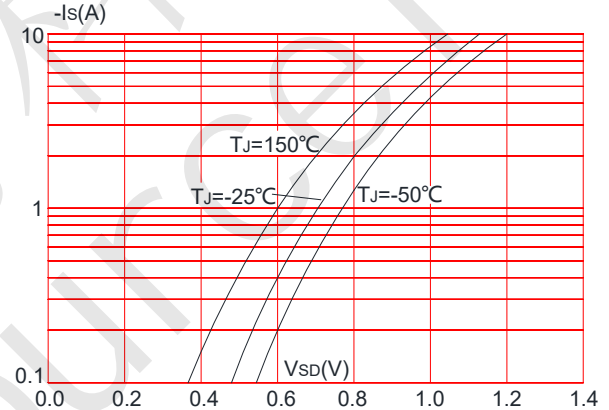


Figure 5: Gate Charge Characteristics

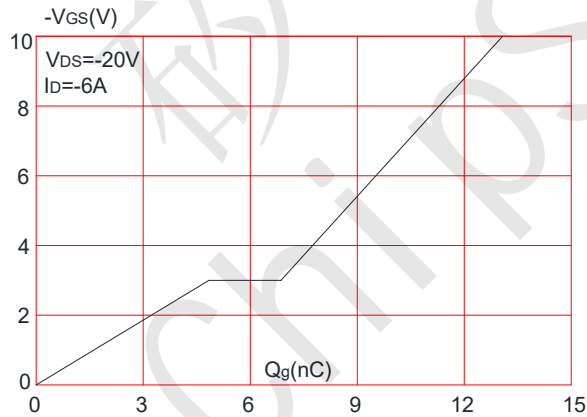
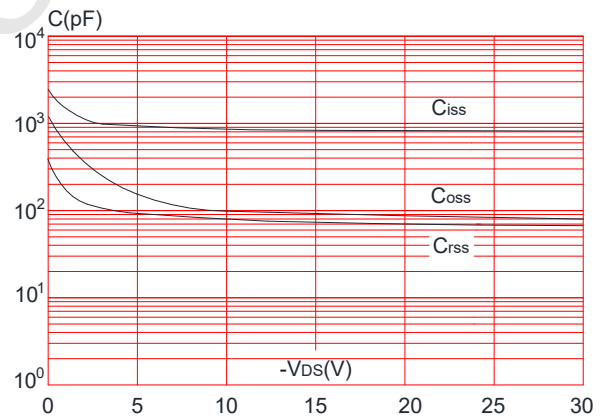


Figure 6: Capacitance Characteristics





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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

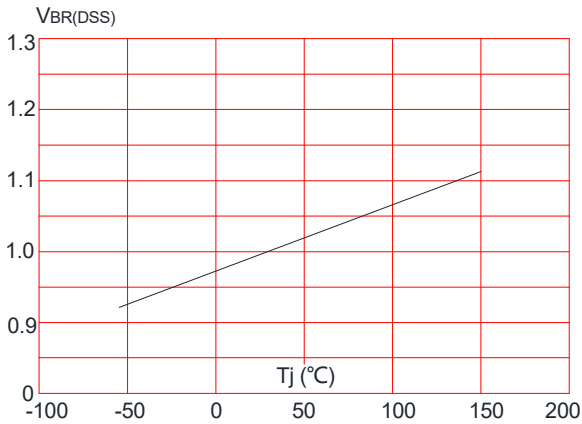


Figure 8: Normalized on Resistance vs. Junction Temperature

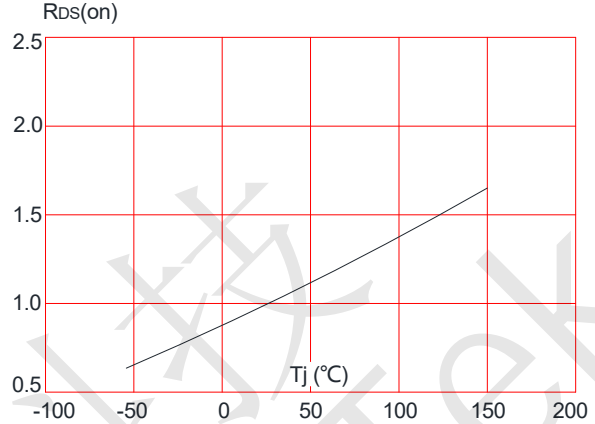


Figure 9: Maximum Safe Operating Area

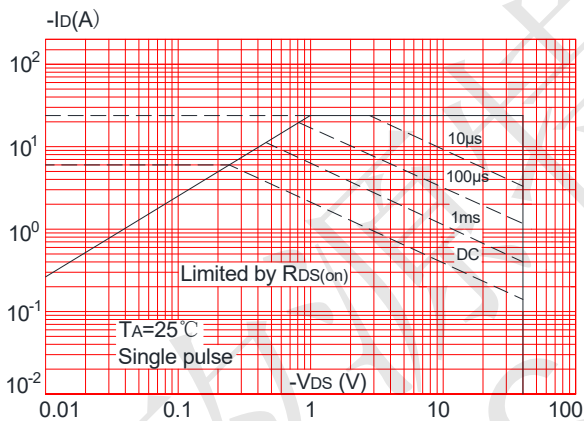


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

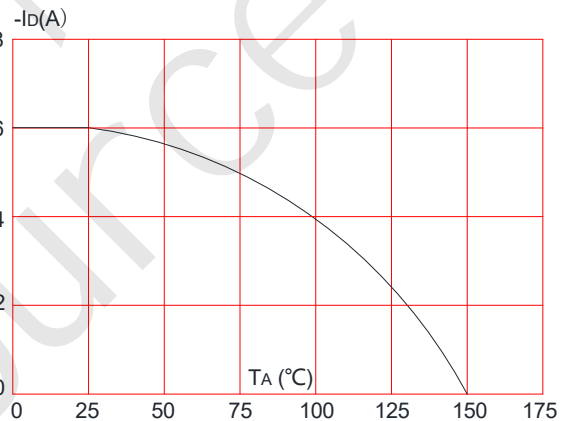
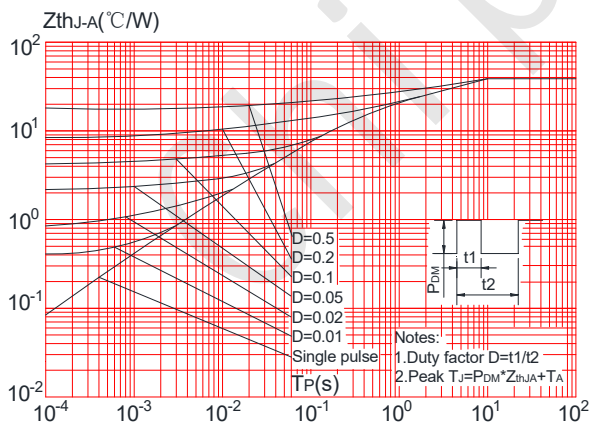
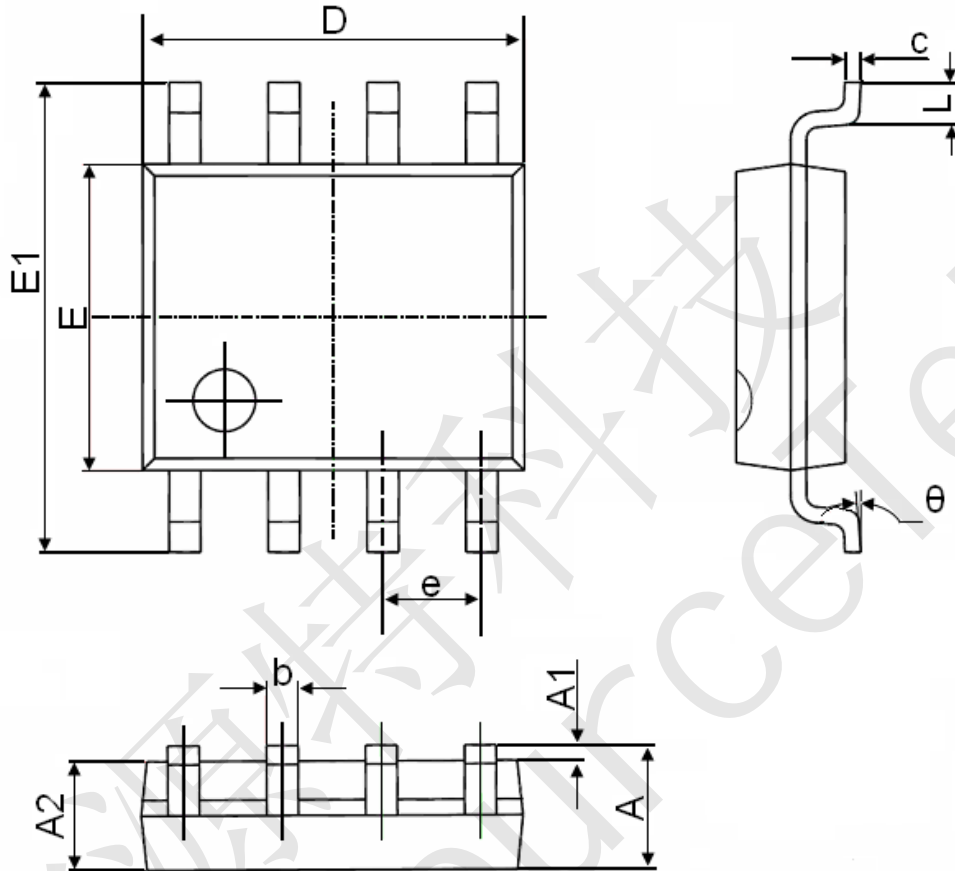


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





CST4614 Package Mechanical Data- SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
theta	0°	8°	0°	8°